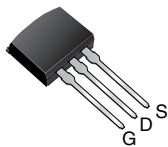


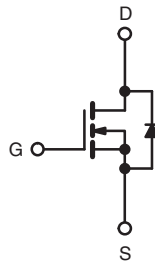
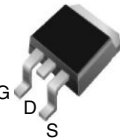
## Power MOSFET

| PRODUCT SUMMARY           |                 |      |
|---------------------------|-----------------|------|
| $V_{DS}$ (V)              | 500             |      |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10$ V | 0.85 |
| $Q_g$ (Max.) (nC)         | 39              |      |
| $Q_{gs}$ (nC)             | 10              |      |
| $Q_{gd}$ (nC)             | 19              |      |
| Configuration             | Single          |      |

I<sup>2</sup>PAK (TO-262)



D<sup>2</sup>PAK (TO-263)



N-Channel MOSFET

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Ultra Low Gate Charge
- Reduced Gate Drive Requirement
- Enhanced 30 V  $V_{GS}$  Rating
- Reduced  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$
- Extremely High Frequency Operation
- Repetitive Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### DESCRIPTION

This new series of low charge Power MOSFETs achieve significantly lower gate charge than conventional Power MOSFETs. Utilizing the new LCDMOS (low charge device Power MOSFETs) technology, the device improvements are achieved without added product cost, allowing for reduced gate drive requirements and total system savings. In addition, reduced switching losses and improved efficiency are achievable in a variety of high frequency applications. Frequencies of a few MHz at high current are possible using the new low charge Power MOSFETs.

These device improvements combined with the proven ruggedness and reliability that characterize Power MOSFETs offer the designer a new power transistor standard for switching applications.

| ORDERING INFORMATION            |                             |                             |
|---------------------------------|-----------------------------|-----------------------------|
| Package                         | D <sup>2</sup> PAK (TO-263) | I <sup>2</sup> PAK (TO-262) |
| Lead (Pb)-free and Halogen-free | SiHF840LCS-GE3              | SiHF840LCL-GE3              |
| Lead (Pb)-free                  | IRF840LCS-PbF               | IRF840LCL-PbF               |
|                                 | SiHF840LCS-E3               | SiHF840LCL-E3               |

#### Note

- a. See device orientation.

| ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted) |                  |                |                  |
|---|------------------|----------------|------------------|
| PARAMETER   | SYMBOL           | LIMIT          | UNIT             |
| Drain-Source Voltage  | $V_{DS}$         | 500            | V                |
| Gate-Source Voltage   | $V_{GS}$         | $\pm 30$       |                  |
| Continuous Drain Current  | $V_{GS}$ at 10 V | $T_C = 25$ °C  | 8.0              |
|   |                  | $T_C = 100$ °C | 5.1              |
| Pulsed Drain Current <sup>a, e</sup>                              |                  | $I_{DM}$       | 28               |
| Linear Derating Factor  |                  |                | 1.0              |
| Single Pulse Avalanche Energy <sup>b, e</sup>                     |                  | $E_{AS}$       | 510              |
| Avalanche Current <sup>a</sup>                                    |                  | $I_{AR}$       | 8.0              |
| Repetitive Avalanche Energy <sup>a</sup>                          |                  | $E_{AR}$       | 13               |
| Maximum Power Dissipation   |                  | $T_C = 25$ °C  | 125              |
|   |                  | $T_A = 25$ °C  | 3.1              |
| Peak Diode Recovery $dV/dt$ <sup>c, e</sup>                       |                  | $dV/dt$        | 3.5              |
| Operating Junction and Storage Temperature Range                  |                  | $T_J, T_{stg}$ | - 55 to + 150    |
| Soldering Recommendations (Peak Temperature)                      |                  | for 10 s       | 300 <sup>d</sup> |

#### Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25$  °C,  $L = 14$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 8.0$  A (see fig. 12).
- $I_{SD} \leq 8.0$  A,  $dI/dt \leq 100$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.
- Uses IRF840LC, SiHF840LC data and test conditions.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS   |            |      |      |      |
|--|------------|------|------|------|
| PARAMETER  | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient (PCB Mounted, Steady-State) <sup>a</sup> | $R_{thJA}$ | -    | 40   | °C/W |
| Maximum Junction-to-Case (Drain)                                     | $R_{thJC}$ | -    | 1.0  |      |

### Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

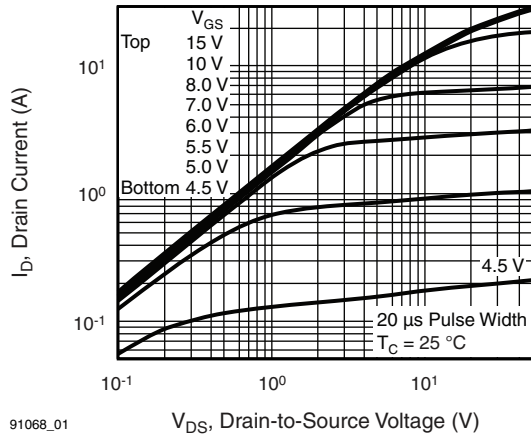
| SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                     |  |      |      |           |               |
|---|---------------------|--|------|------|-----------|---------------|
| PARAMETER   | SYMBOL              | TEST CONDITIONS  | MIN. | TYP. | MAX.      | UNIT          |
| <b>Static</b>   |                     |  |      |      |           |               |
| Drain-Source Breakdown Voltage  | $V_{DS}$            | $V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$   | 500  | -    | -         | V             |
| $V_{DS}$ Temperature Coefficient  | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}^c$  | -    | 0.63 | -         | V/°C          |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$  | 2.0  | -    | 4.0       | V             |
| Gate-Source Leakage   | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$   | -    | -    | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current   | $I_{DSS}$           | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$   | -    | -    | 25        | $\mu\text{A}$ |
|   |                     | $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$  | -    | -    | 250       |               |
| Drain-Source On-State Resistance  | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$   $I_D = 4.8\text{ A}^b$  | -    | -    | 0.85      | $\Omega$      |
| Forward Transconductance  | $g_{fs}$            | $V_{DS} = 50\text{ V}, I_D = 4.8\text{ A}^b$   | 4.0  | -    | -         | S             |
| <b>Dynamic</b>  |                     |  |      |      |           |               |
| Input Capacitance   | $C_{iss}$           | $V_{GS} = 0\text{ V},$<br>$V_{DS} = 25\text{ V},$<br>$f = 1.0\text{ MHz}$ , see fig. 5 <sup>c</sup>  | -    | 1100 | -         | pF            |
| Output Capacitance  | $C_{oss}$           |  | -    | 170  | -         |               |
| Reverse Transfer Capacitance  | $C_{rss}$           |  | -    | 18   | -         |               |
| Total Gate Charge   | $Q_g$               | $V_{GS} = 10\text{ V}$   $I_D = 8.0\text{ A}, V_{DS} = 400\text{ V},$<br>see fig. 6 and 13 <sup>b, c</sup>   | -    | -    | 39        | nC            |
| Gate-Source Charge  | $Q_{gs}$            |  | -    | -    | 10        |               |
| Gate-Drain Charge   | $Q_{gd}$            |  | -    | -    | 19        |               |
| Turn-On Delay Time  | $t_{d(on)}$         | $V_{DD} = 250\text{ V}, I_D = 8.0\text{ A},$<br>$R_g = 9.1\text{ }\Omega, R_D = 30\text{ }\Omega$ , see fig. 10 <sup>b, c</sup>                      | -    | 12   | -         | ns            |
| Rise Time   | $t_r$               |  | -    | 25   | -         |               |
| Turn-Off Delay Time   | $t_{d(off)}$        |  | -    | 27   | -         |               |
| Fall Time   | $t_f$               |  | -    | 19   | -         |               |
| <b>Drain-Source Body Diode Characteristics</b>                              |                     |  |      |      |           |               |
| Continuous Source-Drain Diode Current                                       | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode  | -    | -    | 8.0       | A             |
| Pulsed Diode Forward Current <sup>a</sup>                                   | $I_{SM}$            |  | -    | -    | 28        |               |
| Body Diode Voltage  | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}, I_S = 8.0\text{ A}, V_{GS} = 0\text{ V}^b$  | -    | -    | 2.0       | V             |
| Body Diode Reverse Recovery Time  | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}, I_F = 8.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b, c$  | -    | 490  | 740       | ns            |
| Body Diode Reverse Recovery Charge  | $Q_{rr}$            |  | -    | 3.0  | 4.5       | $\mu\text{C}$ |
| Forward Turn-On Time  | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )  |      |      |           |               |

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- Uses SiHF840LC data and test conditions.

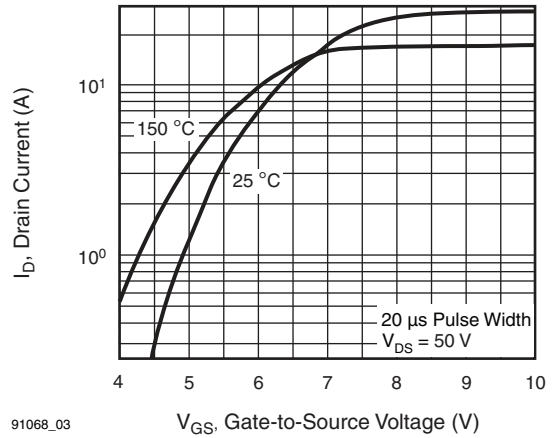


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



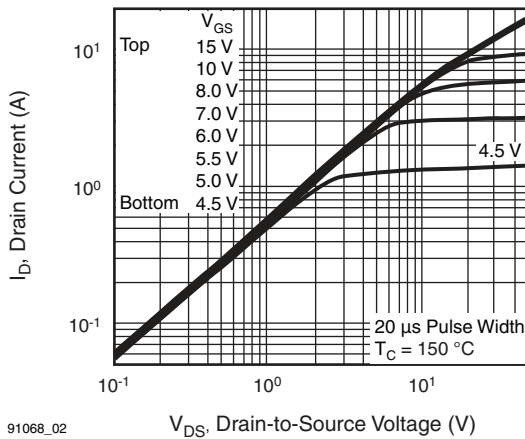
91068\_01

**Fig. 1 - Typical Output Characteristics**



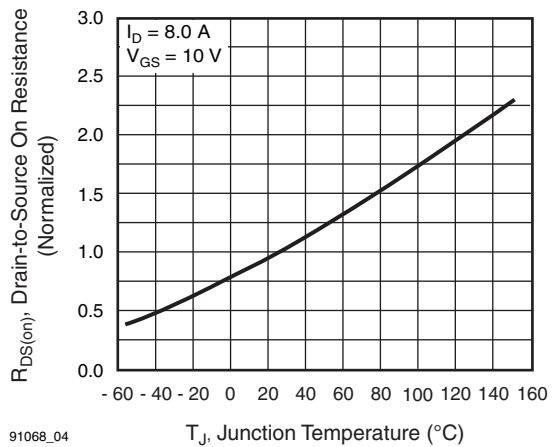
91068\_03

**Fig. 3 - Typical Transfer Characteristics**



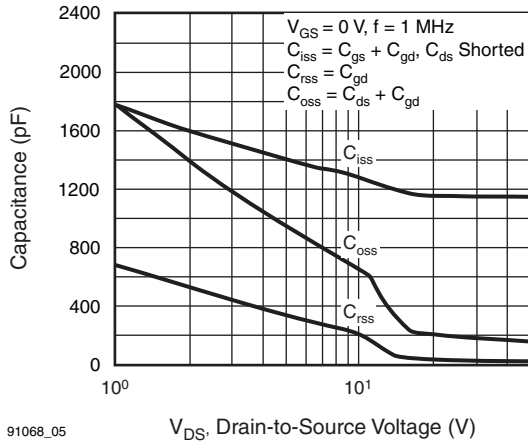
91068\_02

**Fig. 2 - Typical Output Characteristics**



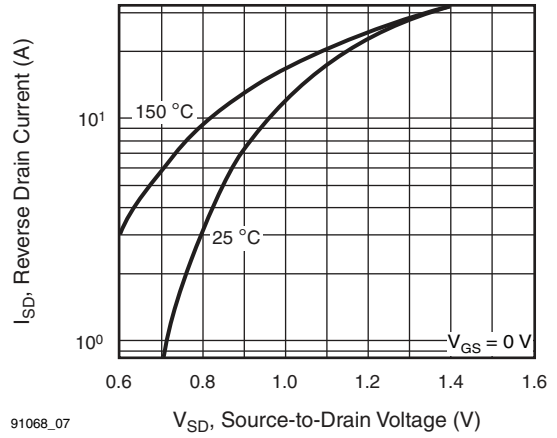
91068\_04

**Fig. 4 - Normalized On-Resistance vs. Temperature**



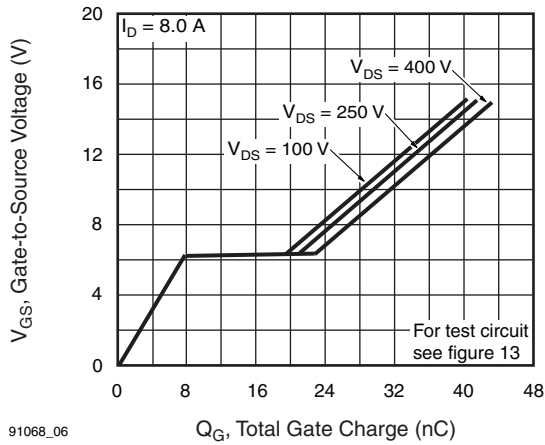
91068\_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



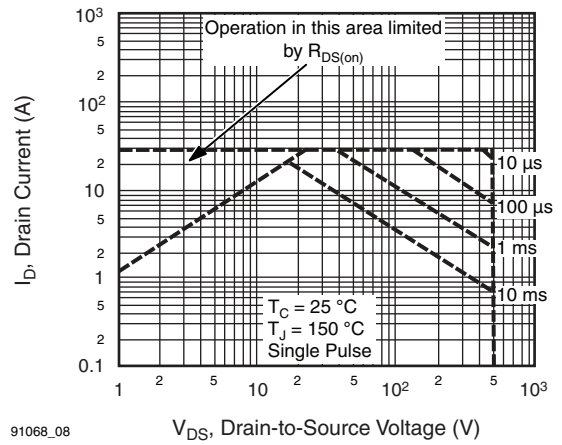
91068\_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



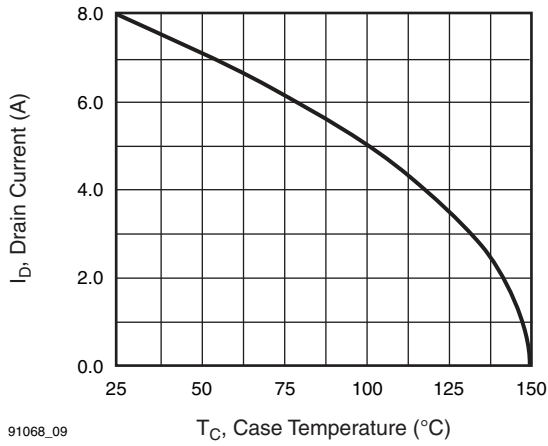
91068\_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91068\_08

Fig. 8 - Maximum Safe Operating Area



91068\_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

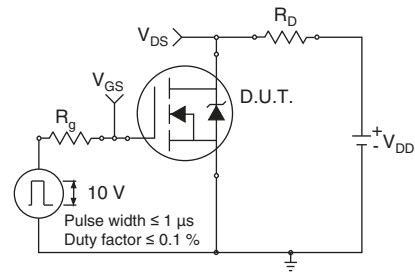


Fig. 10a - Switching Time Test Circuit

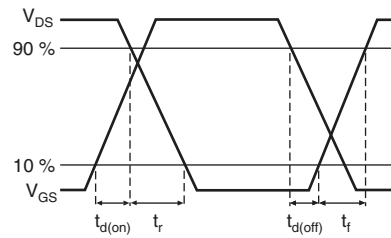
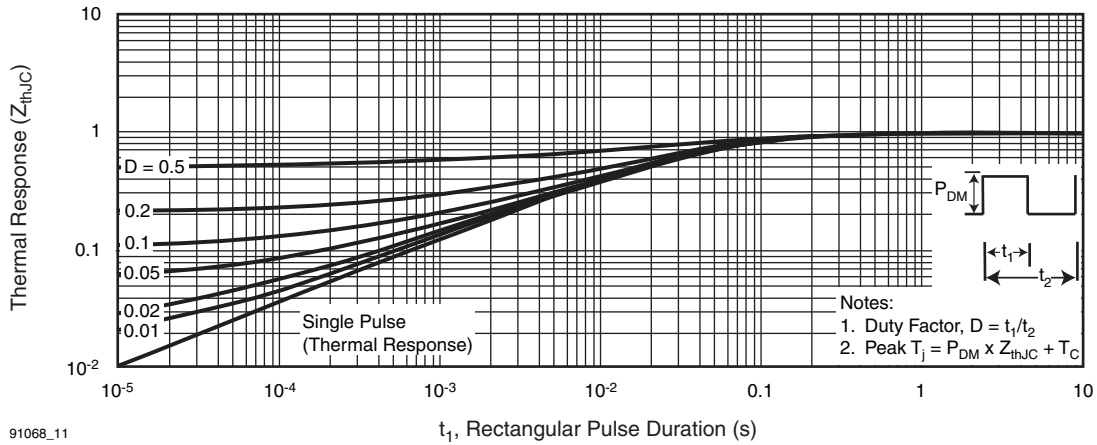


Fig. 10b - Switching Time Waveforms



91068\_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

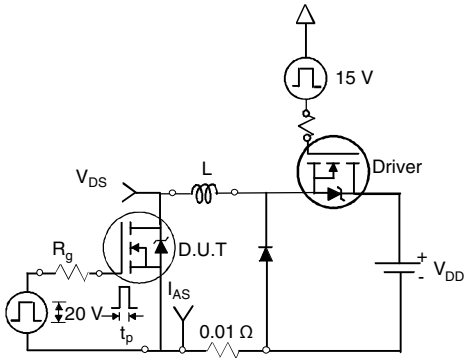


Fig. 12a - Unclamped Inductive Test Circuit

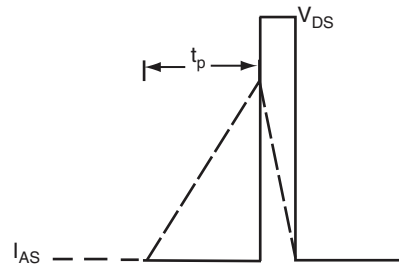


Fig. 12b - Unclamped Inductive Waveforms

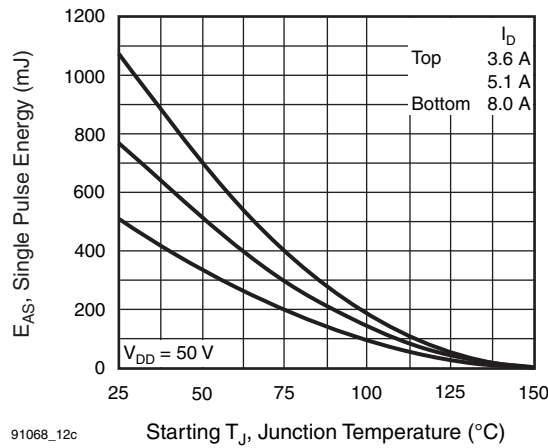


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

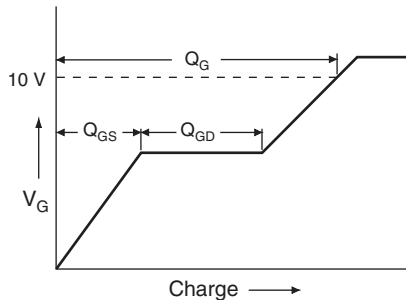


Fig. 13a - Basic Gate Charge Waveform

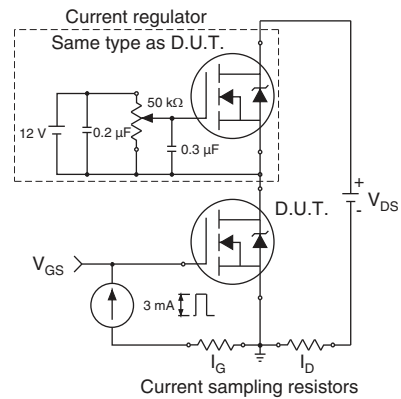
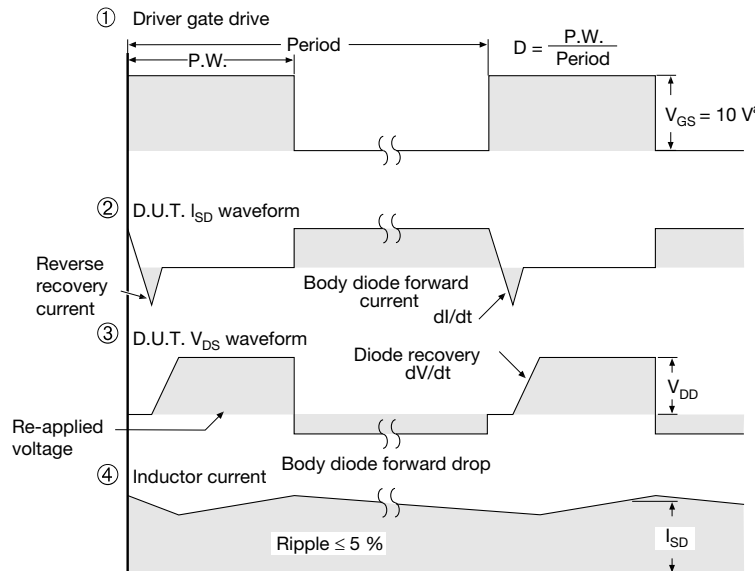
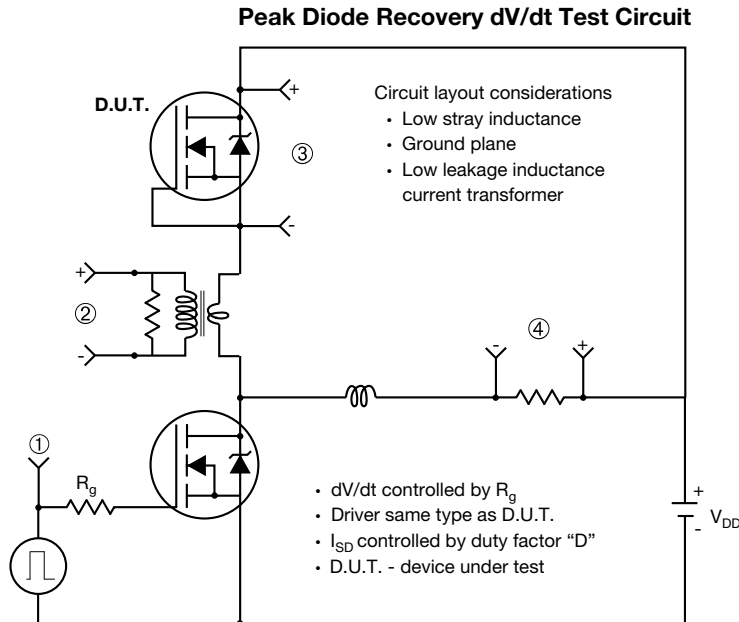


Fig. 13b - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91068](http://www.vishay.com/ppg?91068).

### TO-263AB (HIGH VOLTAGE)



| DIM. | MILLIMETERS |      | INCHES |       |
|------|-------------|------|--------|-------|
|      | MIN.        | MAX. | MIN.   | MAX.  |
| A    | 4.06        | 4.83 | 0.160  | 0.190 |
| A1   | 0.00        | 0.25 | 0.000  | 0.010 |
| b    | 0.51        | 0.99 | 0.020  | 0.039 |
| b1   | 0.51        | 0.89 | 0.020  | 0.035 |
| b2   | 1.14        | 1.78 | 0.045  | 0.070 |
| b3   | 1.14        | 1.73 | 0.045  | 0.068 |
| c    | 0.38        | 0.74 | 0.015  | 0.029 |
| c1   | 0.38        | 0.58 | 0.015  | 0.023 |
| c2   | 1.14        | 1.65 | 0.045  | 0.065 |
| D    | 8.38        | 9.65 | 0.330  | 0.380 |

| DIM. | MILLIMETERS |       | INCHES    |       |
|------|-------------|-------|-----------|-------|
|      | MIN.        | MAX.  | MIN.      | MAX.  |
| D1   | 6.86        | -     | 0.270     | -     |
| E    | 9.65        | 10.67 | 0.380     | 0.420 |
| E1   | 6.22        | -     | 0.245     | -     |
| e    | 2.54 BSC    |       | 0.100 BSC |       |
| H    | 14.61       | 15.88 | 0.575     | 0.625 |
| L    | 1.78        | 2.79  | 0.070     | 0.110 |
| L1   | -           | 1.65  | -         | 0.066 |
| L2   | -           | 1.78  | -         | 0.070 |
| L3   | 0.25 BSC    |       | 0.010 BSC |       |
| L4   | 4.78        | 5.28  | 0.188     | 0.208 |

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## Material Category Policy

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.